FKBB0210

Dual N-Ch 100V Fast Switching MOSFETs

Features

- Advanced Trench MOS Technology
- Low $R_{DS(ON)}$
- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available

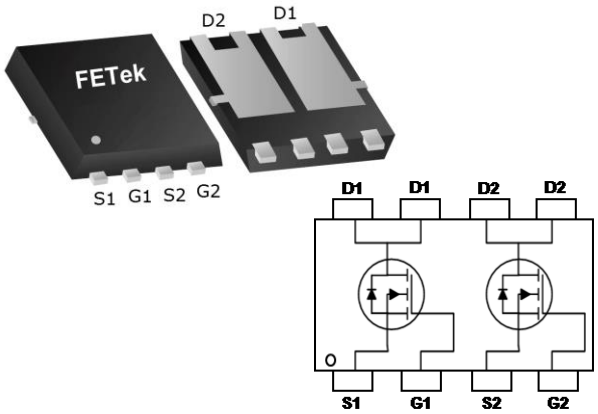
Product Summary

BVDSS	RDSON	ID
100V	100mΩ	8A

Application

- Portable Equipment.
- Battery Powered Systems.
- Hard Switching and High-Speed Circuit.

PRPAK3x3 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25°C	Continuous Drain Current, V_{GS} @ 10V[1]	8	A
I_D@T_C=100°C	Continuous Drain Current, V_{GS} @ 10V[1]	5	A
I_D@T_A=25°C	Continuous Drain Current, V_{GS} @ 10V[1]	2.8	A
I_D@T_A=70°C	Continuous Drain Current, V_{GS} @ 10V[1]	2.3	A
I_{DM}	Pulsed Drain Current[2]	24	A
EAS	Single Pulse Avalanche Energy[3]	0.22	mJ
I_{AS}	Avalanche Current	2.1	A
P_D@T_C=25°C	Total Power Dissipation[4]	12.5	W
P_D@T_A=25°C	Total Power Dissipation[4]	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1]	---	85	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	10	°C/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=2A	---	89	100	mΩ
		V_{GS}=4.5V , I_D=2A	---	113	130	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.3	1.6	2.3	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=80V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=80V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	5	---	Ω
Q_g	Total Gate Charge	V_{DS}=50V , V_{GS}=10V , I_D=2A	---	3.49	---	nC
Q_{gs}	Gate-Source Charge		---	0.66	---	
Q_{gd}	Gate-Drain Charge		---	0.92	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=50V , V_{GS}=10V , R_G=3Ω, I_D=1A	---	4.8	---	ns
T_r	Rise Time		---	19	---	
$T_{d(off)}$	Turn-Off Delay Time		---	17	---	
T_f	Fall Time		---	6.2	---	
C_{iss}	Input Capacitance	V_{DS}=50V , V_{GS}=0V , f=1MHz	---	180	---	pF
C_{oss}	Output Capacitance		---	32	---	
C_{rss}	Reverse Transfer Capacitance		---	2.5	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	8	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=2.1A
4.The power dissipation is limited by 150℃ junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

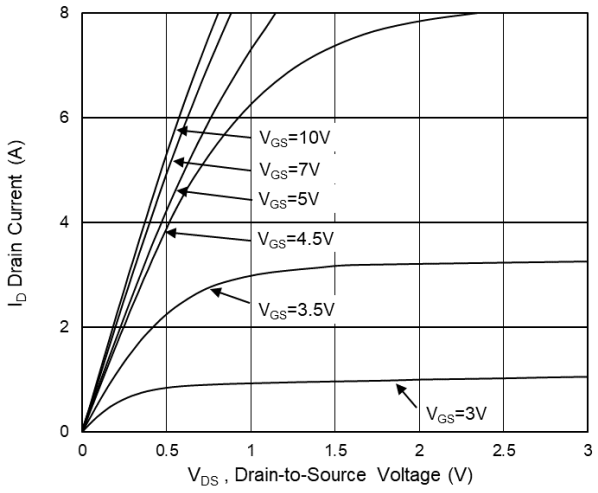


Fig.1 Typical Output Characteristics

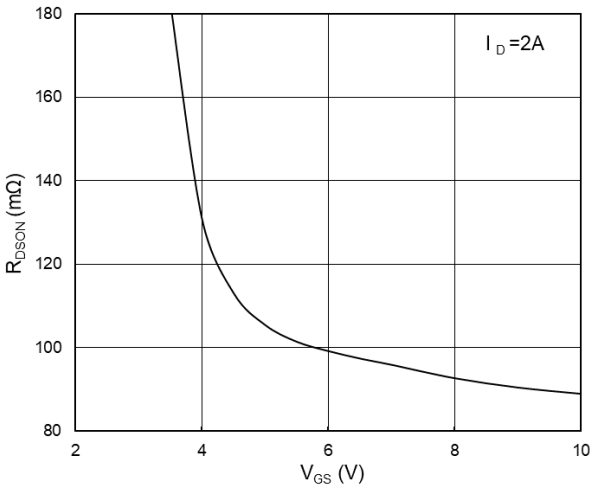


Fig.2 On-Resistance vs G-S Voltage

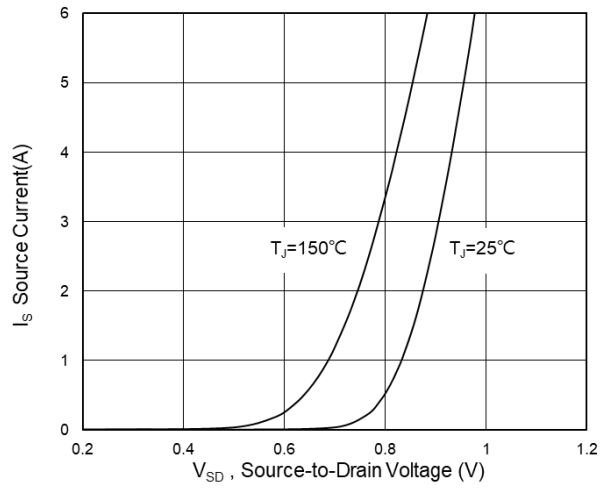


Fig.3 Source Drain Forward Characteristics

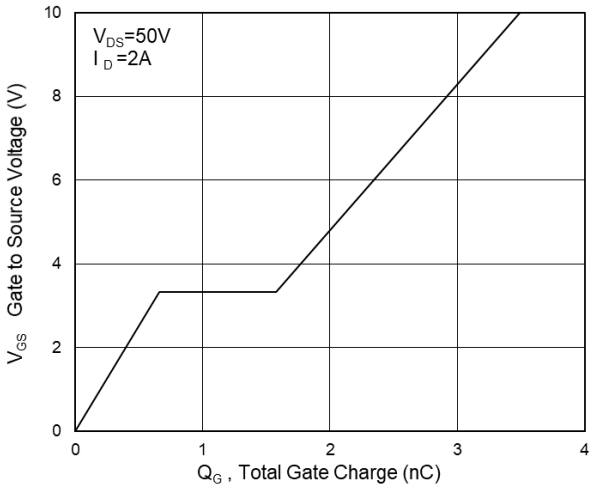


Fig.4 Gate-Charge Characteristics

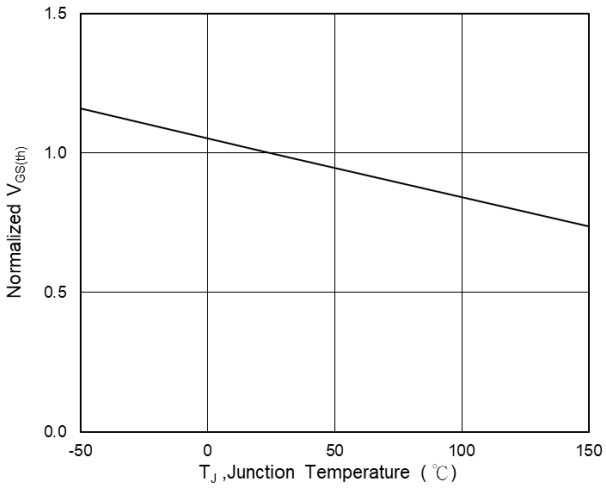


Fig.5 Normalized $V_{GS(th)}$ vs T_J

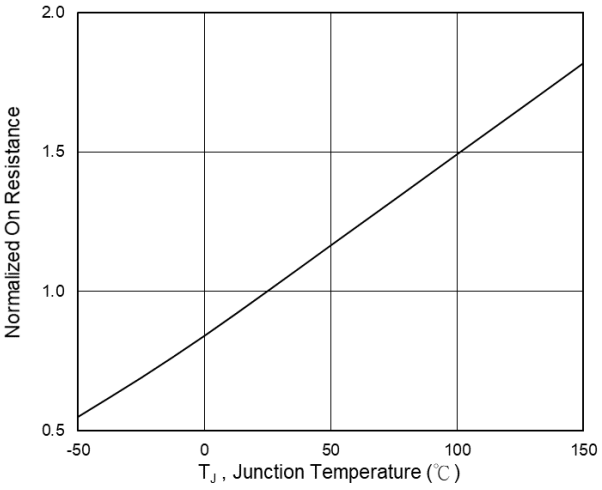


Fig.6 Normalized R_{DSON} vs T_J

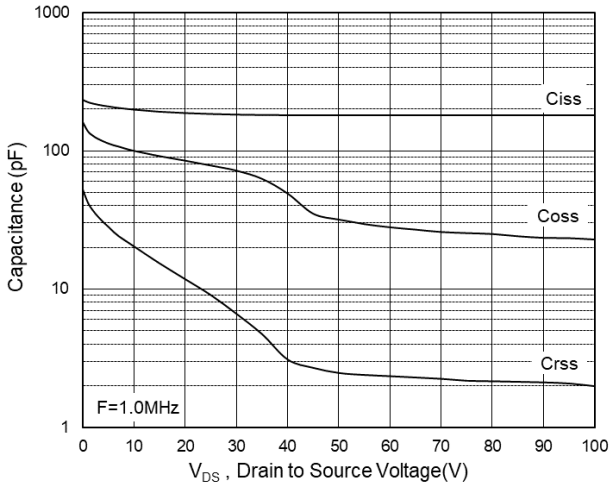


Fig.7 Capacitance

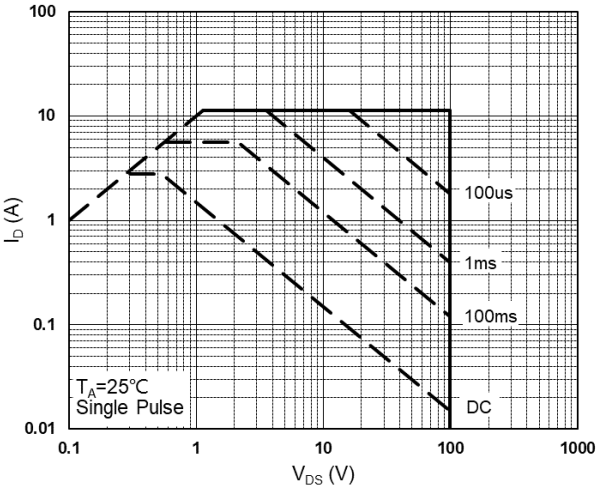


Fig.8 Safe Operating Area

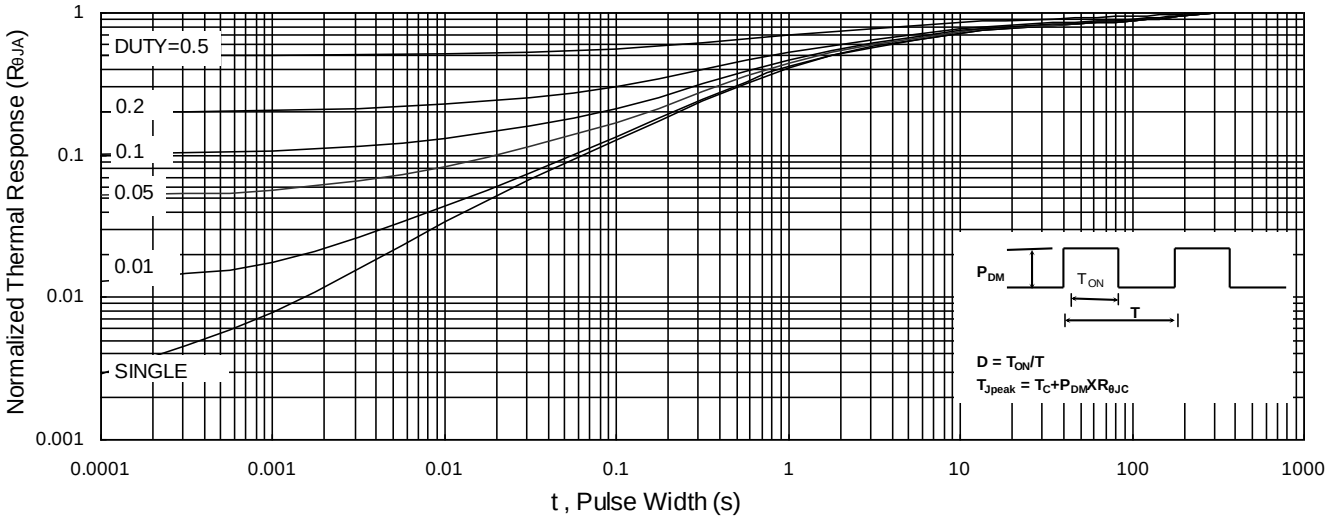


Fig.9 Normalized Maximum Transient Thermal Impedance

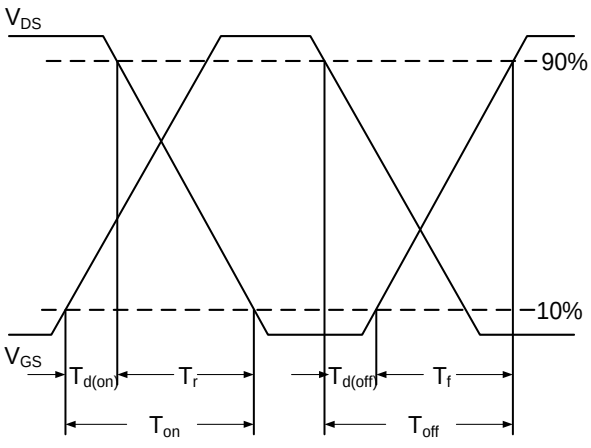


Fig.10 Switching Time Waveform

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS}-V_{DD}}$$

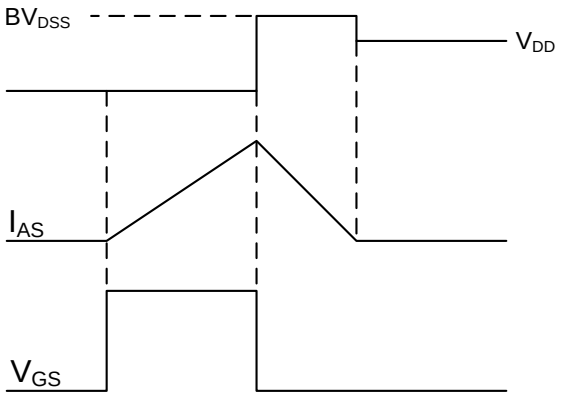


Fig.11 Unclamped Inductive Waveform